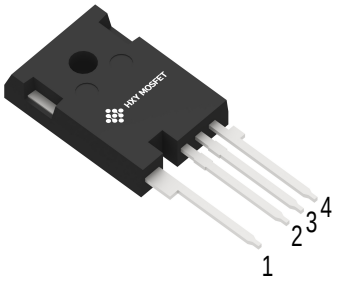
HTW083Z65C

SiC Power MOSFET N-Channel Enhancement Mode

Features

- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant



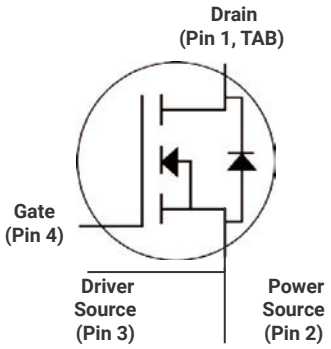
TO-247H-4L

Benefits

- Reduce switching losses and minimize gate ringing
- Higher system effciency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies



Ordering Part Number	Package	Qty(PCS)
HTW083Z65C	TO-247H-4L	30

Maximum Ratings (T_C = 25 °C unless otherwise specifed)

Symbol	Parameter	Value	Unit	Note
V_{DSS}	Drain - Source Voltage, T_C = 25 ˚C	650	V	
V_{GS}	Gate - Source voltage (Under transient events < 100 ns)	-8/+19	V	Fig. 29
I_D	Continuous Drain Current, V_{GS} = 15 V, T_C = 25˚C	37	A	Fig. 19
	Continuous Drain Current, V_{GS} = 15 V, T_C = 100˚C	27		
$I_{D(pulse)}$	Pulsed Drain Current, Pulse width t_P limited by T_{jmax}	99	A	
P_D	Power Dissipation, T_C=25˚C, T_J = 175 ˚C	150	W	Fig. 20
T_J , T_{stg}	Operating Junction and Storage Temperature	-40 to +175	˚C	
T_L	Solder Temperature, 1.6mm (0.063") from case for 10s	260	˚C	
M_d	Mounting Torque, (M3 or 6-32 screw)	1 8.8	Nm lbf-in	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650			V	V_{GS} = 0 V, I_D = 100 μA	
V_{GSon}	Gate-Source Recommended Turn-On Voltage		15		V	Static	Fig. 29
V_{GSoff}	Gate-Source Recommended Turn-Off Voltage		-4		V		
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.3	3.6	V	V_{DS} = V_{GS}, I_D = 5 mA	Fig. 11
			1.9		V	V_{DS} = V_{GS}, I_D = 5 mA, T_J = 175ºC	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	μA	V_{DS} = 650 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance	42	60	79	mΩ	V_{GS} = 15 V, I_D = 13.2 A	Fig. 4, 5,6
			80			V_{GS} = 15 V, I_D = 13.2 A, T_J = 175ºC	
g_{fs}	Transconductance		10		S	V_{DS}= 20 V, I_{DS}= 13.2 A	Fig. 7
			9			V_{DS}= 20 V, I_{DS}= 13.2 A, T_J = 175ºC	
C_{iss}	Input Capacitance		1020		pF	V_{GS} = 0 V, V_{DS} = 600 V f = 1 MHz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		80				
C_{rss}	Reverse Transfer Capacitance		9				
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		95		pF	V_{GS} = 0 V, V_{DS} = 0V to 400 V	Note 1
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		132				
E_{oss}	C_{oss} Stored Energy		15		μJ	V_{DS} = 600 V, 1 MHz	Fig. 16
E_{ON}	Turn-On Switching Energy (Body Diode)		70		μJ	V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 13.2 A, $R_{G(ext)}$ = 2.5Ω, L= 135 μH, T_J = 175ºC FWD = Internal Body Diode of MOSFET	Fig. 25
E_{OFF}	Turn Off Switching Energy (Body Diode)		5				
E_{ON}	Turn-On Switching Energy (External SiC Diode)		67		μJ	V_{DS} = 400 V, V_{GS} = -4 V/15 V, I_D = 13.2 A, $R_{G(ext)}$ = 2.5Ω, L= 135 μH, T_J = 175ºC FWD = External SiC Diode	Fig. 25
E_{OFF}	Turn Off Switching Energy (External SiC Diode)		6				
$t_{d(on)}$	Turn-On Delay Time		8		ns	V_{DD} = 400 V, V_{GS} = -4 V/15 V I_D = 13.2 A, $R_{G(ext)}$ = 2.5 Ω, L= 135 μH Timing relative to V_{DS} Inductive load	Fig. 26
t_r	Rise Time		11				
$t_{d(off)}$	Turn-Off Delay Time		17				
t_f	Fall Time		5				
$R_{G(int)}$	Internal Gate Resistance		3		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		13		nC	V_{DS} = 400 V, V_{GS} = -4 V/15 V I_D = 13.2 A Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		17				
Q_g	Total Gate Charge		46				

Note (1): $C_{o(er)}$, a lumped capacitance that gives same stored energy as Coss while Vds is rising from 0 to 400V
$C_{o(tr)}$, a lumped capacitance that gives same charging time as Coss while Vds is rising from 0 to 400V

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	5.1		V	V_{GS} = -4 V, I_{SD} = 6.6 A, T_J = 25 °C	Fig. 8, 9, 10
		4.8		V	V_{GS} = -4 V, I_{SD} = 6.6 A, T_J = 175 °C	
I_S	Continuous Diode Forward Current		23	A	V_{GS} = -4 V, T_C = 25˚C	
$I_{S,\ pulse}$	Diode pulse Current		99	A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	
t_{rr}	Reverse Recover time	11		ns	V_{GS} = -4 V, I_{SD} = 13.2 A, V_R = 400 V dif/dt = 4500 A/μs, T_J = 175 °C	
Q_{rr}	Reverse Recovery Charge	151		nC		
I_{rrm}	Peak Reverse Recovery Current	27		A		
t_{rr}	Reverse Recover time	16		ns	V_{GS} = -4 V, I_{SD} = 13.2 A, V_R = 400 V dif/dt = 2400 A/μs, T_J = 175 °C	
Q_{rr}	Reverse Recovery Charge	110		nC		
I_{rrm}	Peak Reverse Recovery Current	12		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.99	°C/W		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	40			

Typical Performance Characteristics

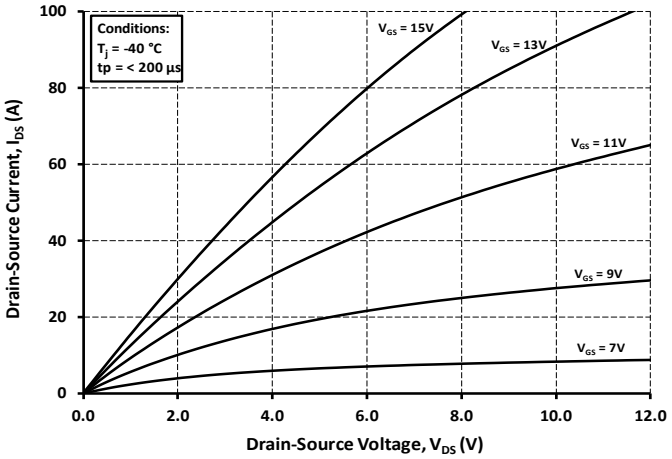


Figure 1. Output Characteristics T_J = -40 ºC

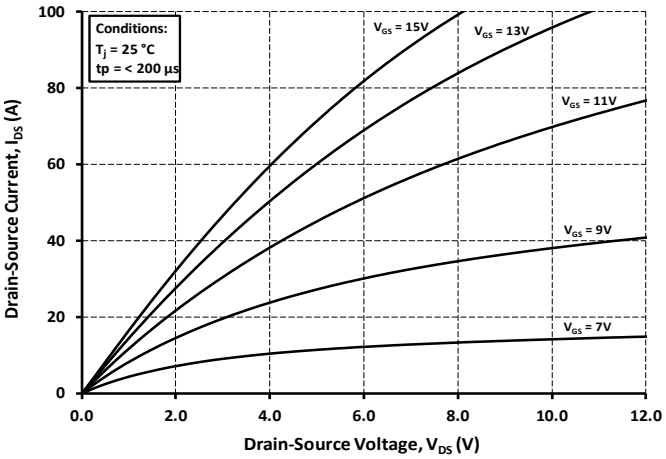


Figure 2. Output Characteristics T_J = 25 ºC

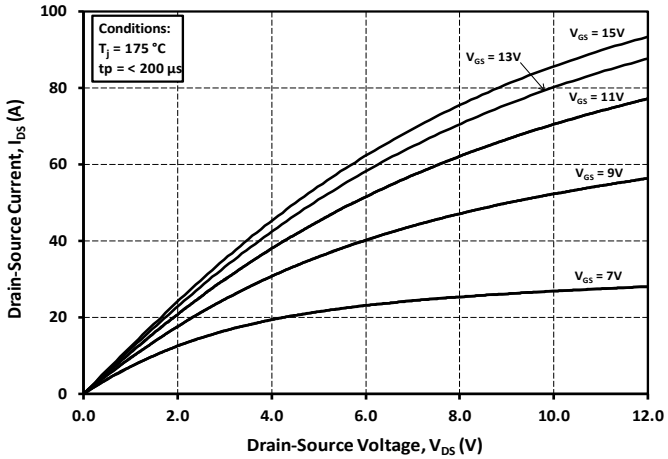


Figure 3. Output Characteristics T_J = 175 ºC

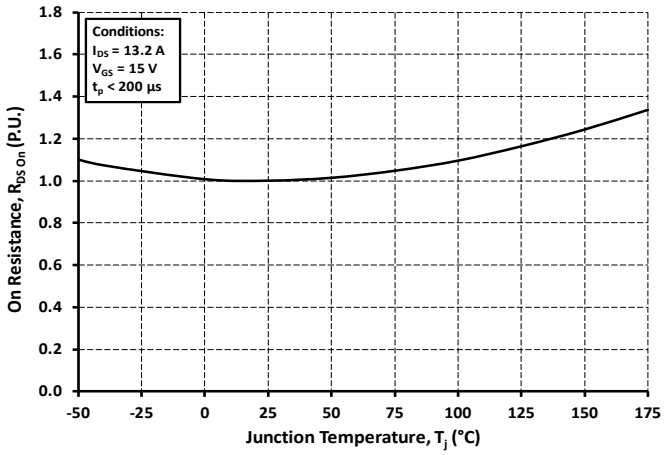


Figure 4. Normalized On-Resistance vs. Temperature

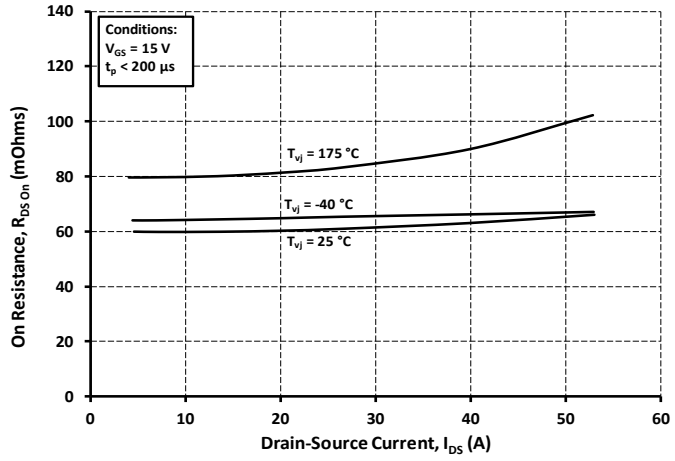


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

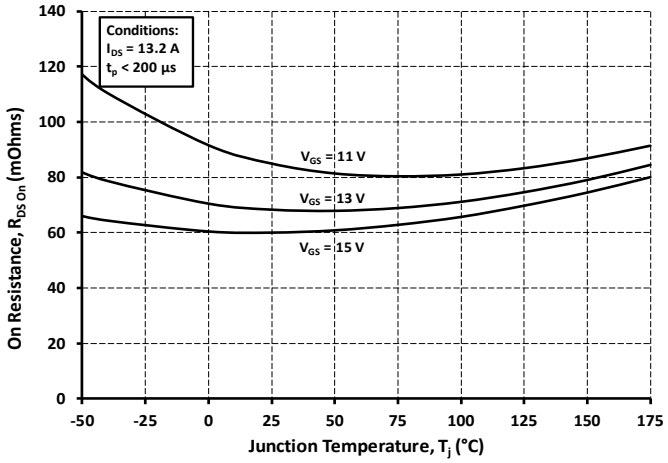


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

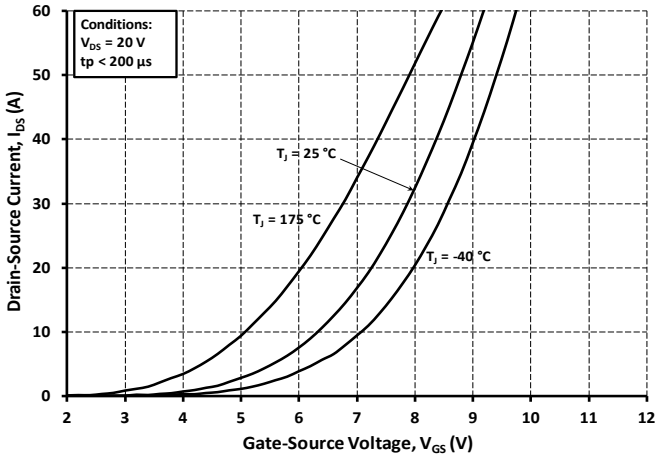


Figure 7. Transfer Characteristic for Various Junction Temperatures

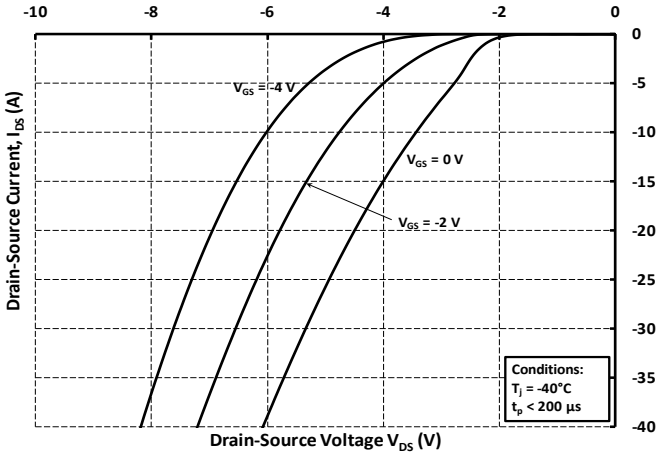


Figure 8. Body Diode Characteristic at -40 °C

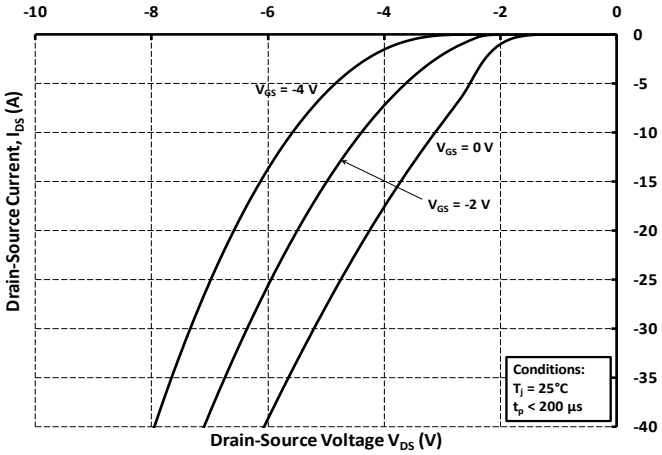


Figure 9. Body Diode Characteristic at 25 °C

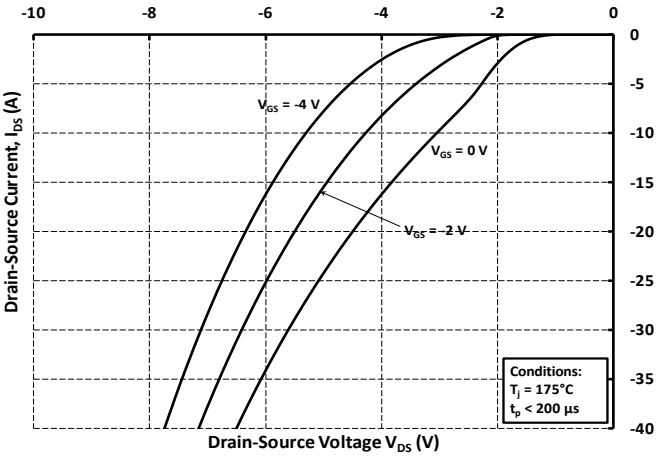


Figure 10. Body Diode Characteristic at 175 °C

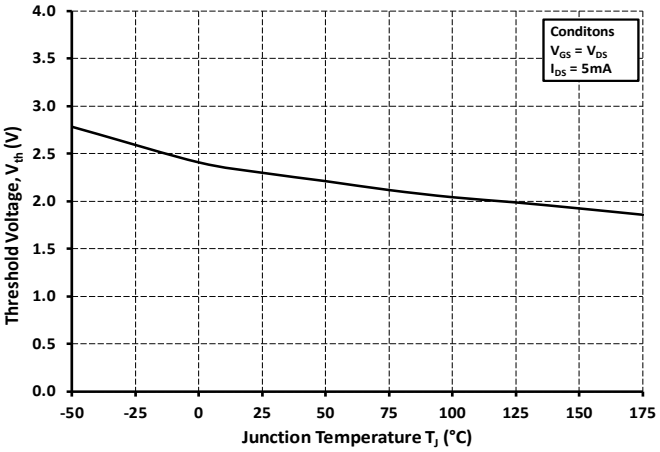


Figure 11. Threshold Voltage vs. Temperature

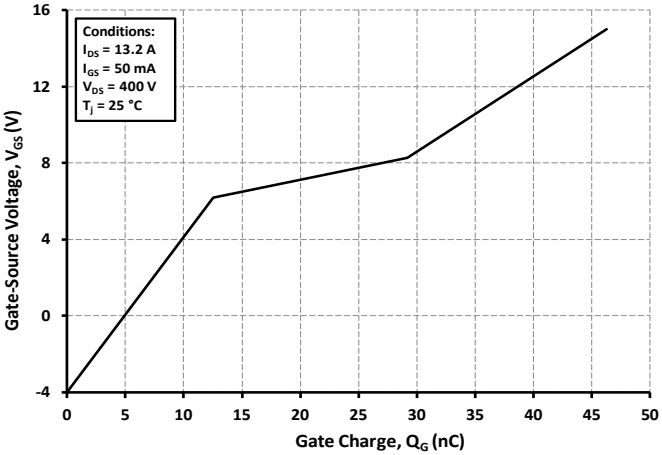


Figure 12. Gate Charge Characteristics

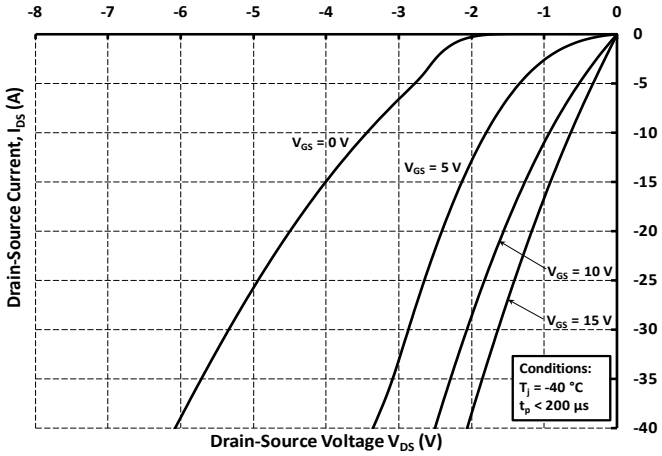


Figure 13. 3rd Quadrant Characteristic at -40 °C

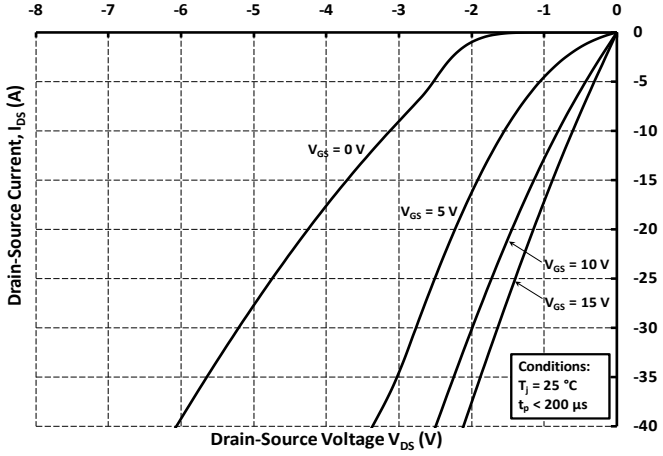


Figure 14. 3rd Quadrant Characteristic at 25 °C

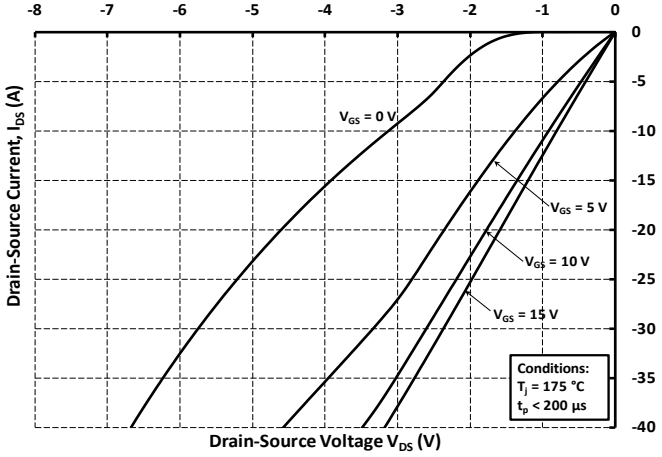


Figure 15. 3rd Quadrant Characteristic at 175 °C

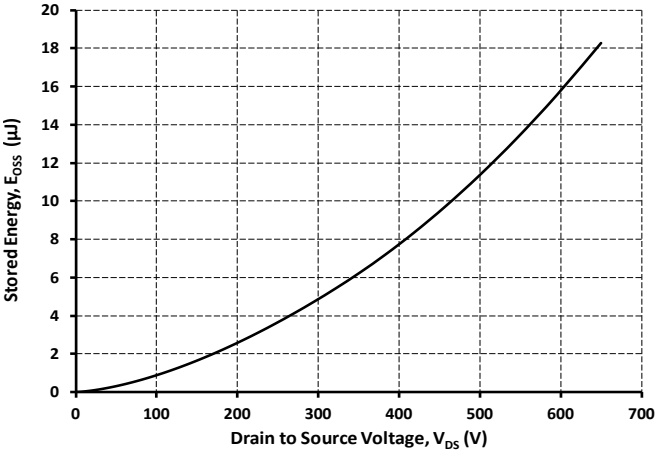


Figure 16. Output Capacitor Stored Energy

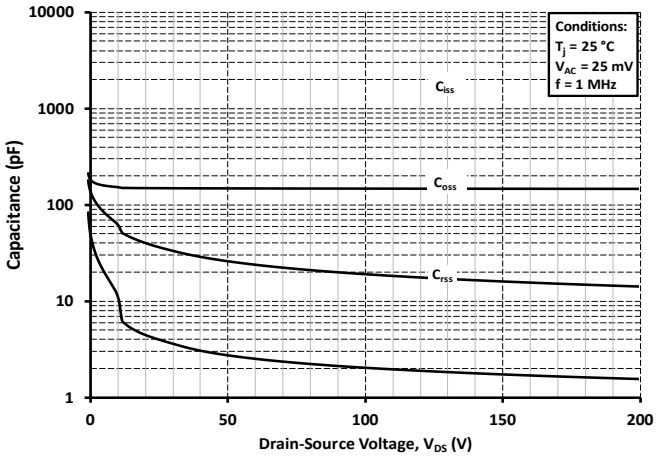


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

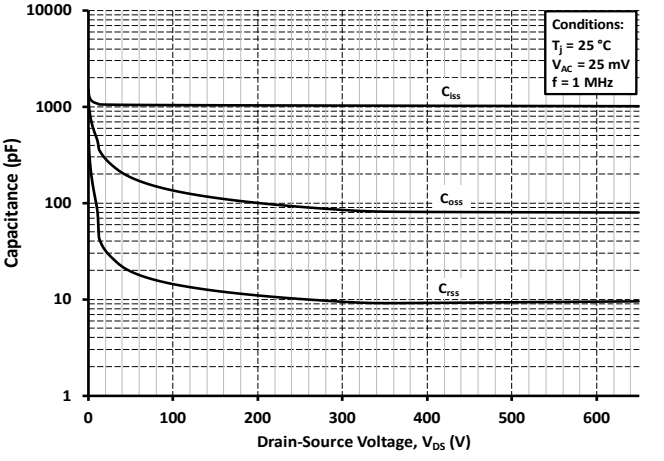


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 650V)

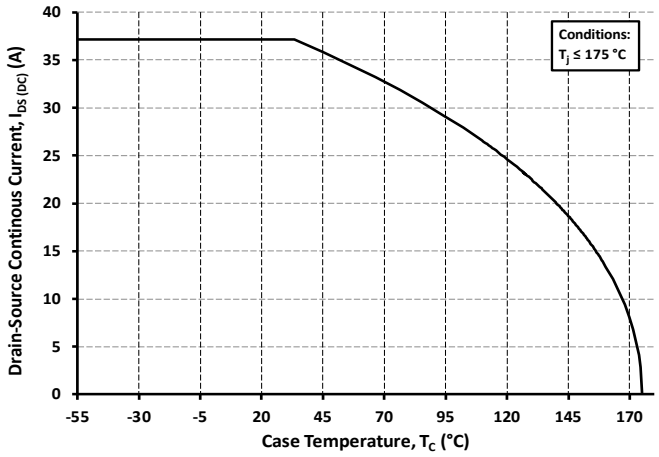


Figure 19. Continuous Drain Current Derating vs. Case Temperature

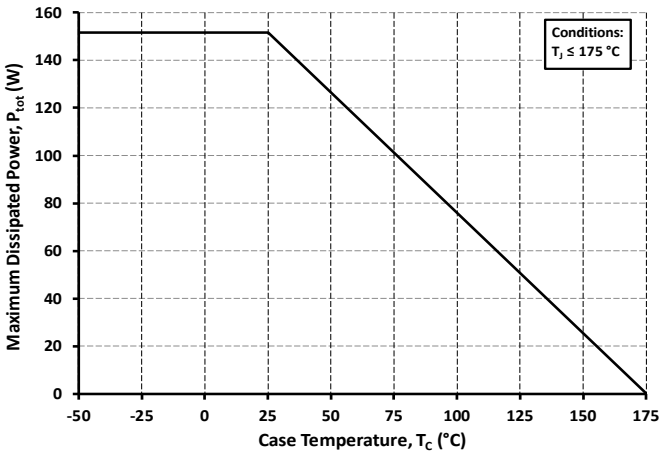


Figure 20. Maximum Power Dissipation Derating Vs Case Temperature

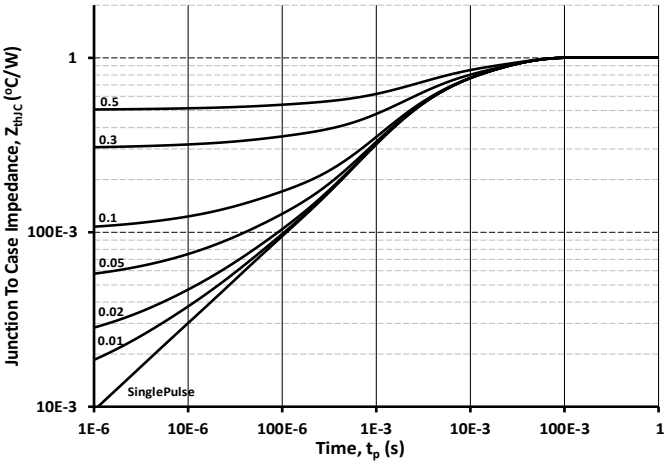


Figure 21. Transient Thermal Impedance (Junction - Case)

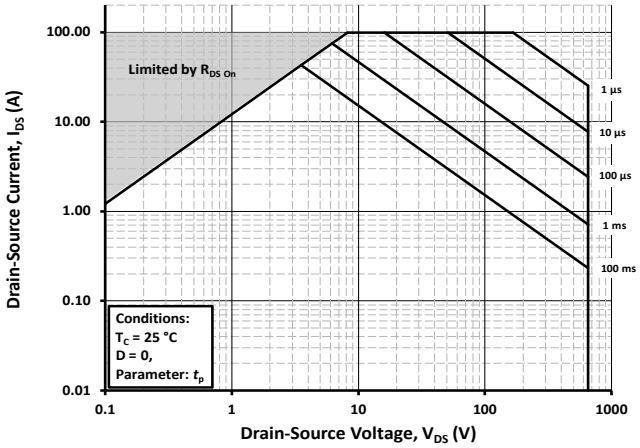


Figure 22. Safe Operating Area

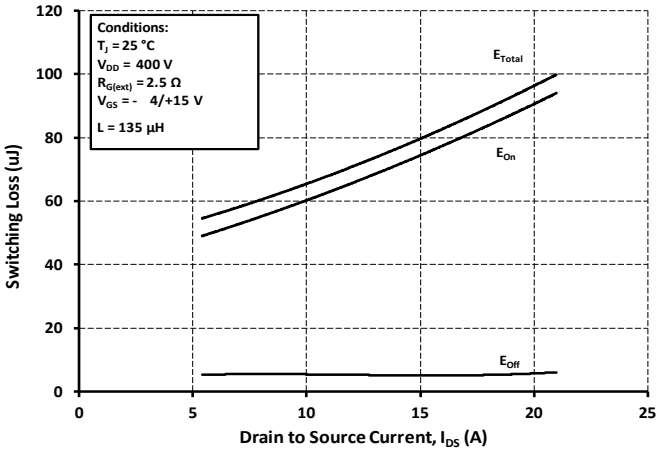


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 400V)

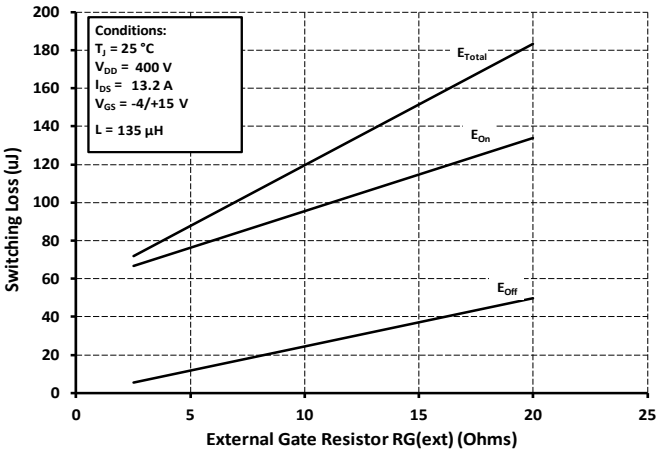


Figure 24. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

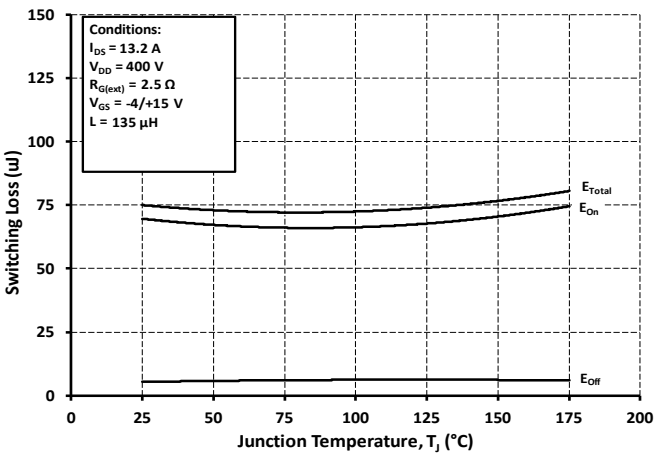


Figure 25. Clamped Inductive Switching Energy vs. Temperature

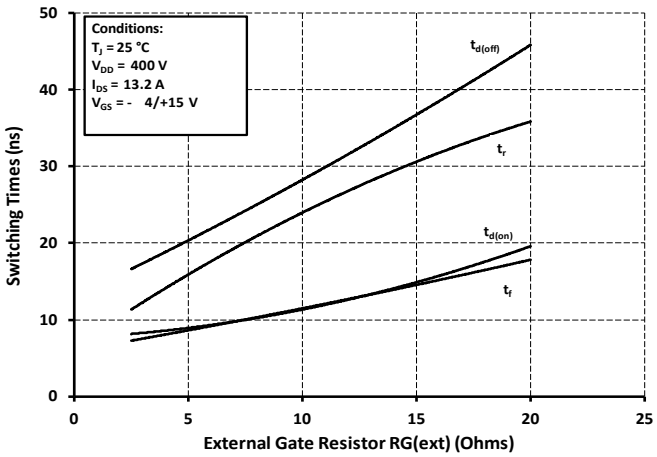


Figure 26. Switching Times vs. $R_{G(ext)}$

Test Circuit Schematic

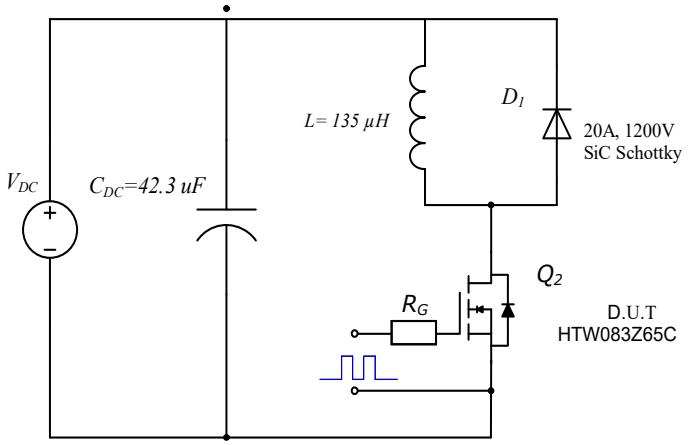


Figure 27. Clamped Inductive Switching Waveform Test Circuit

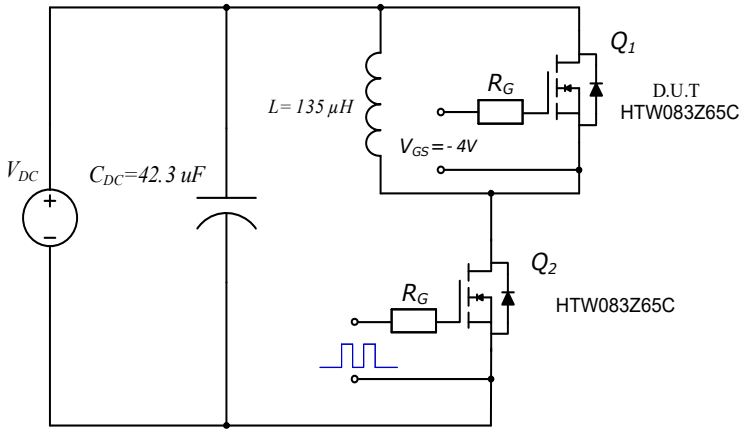


Figure 28. Body Diode Recovery Test Circuit

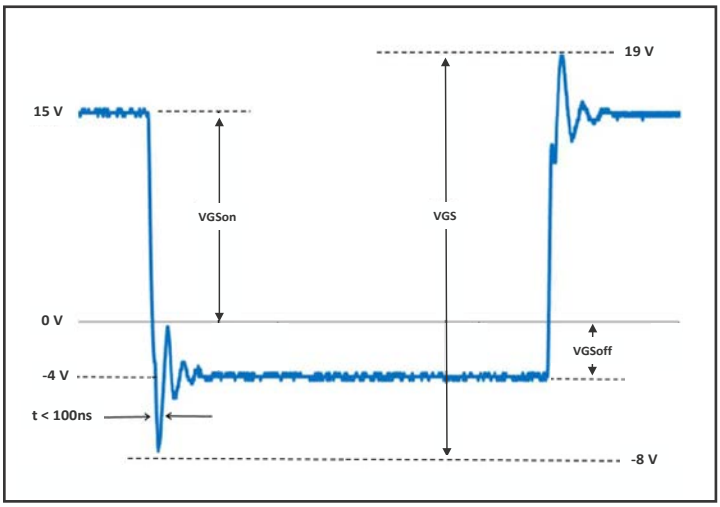
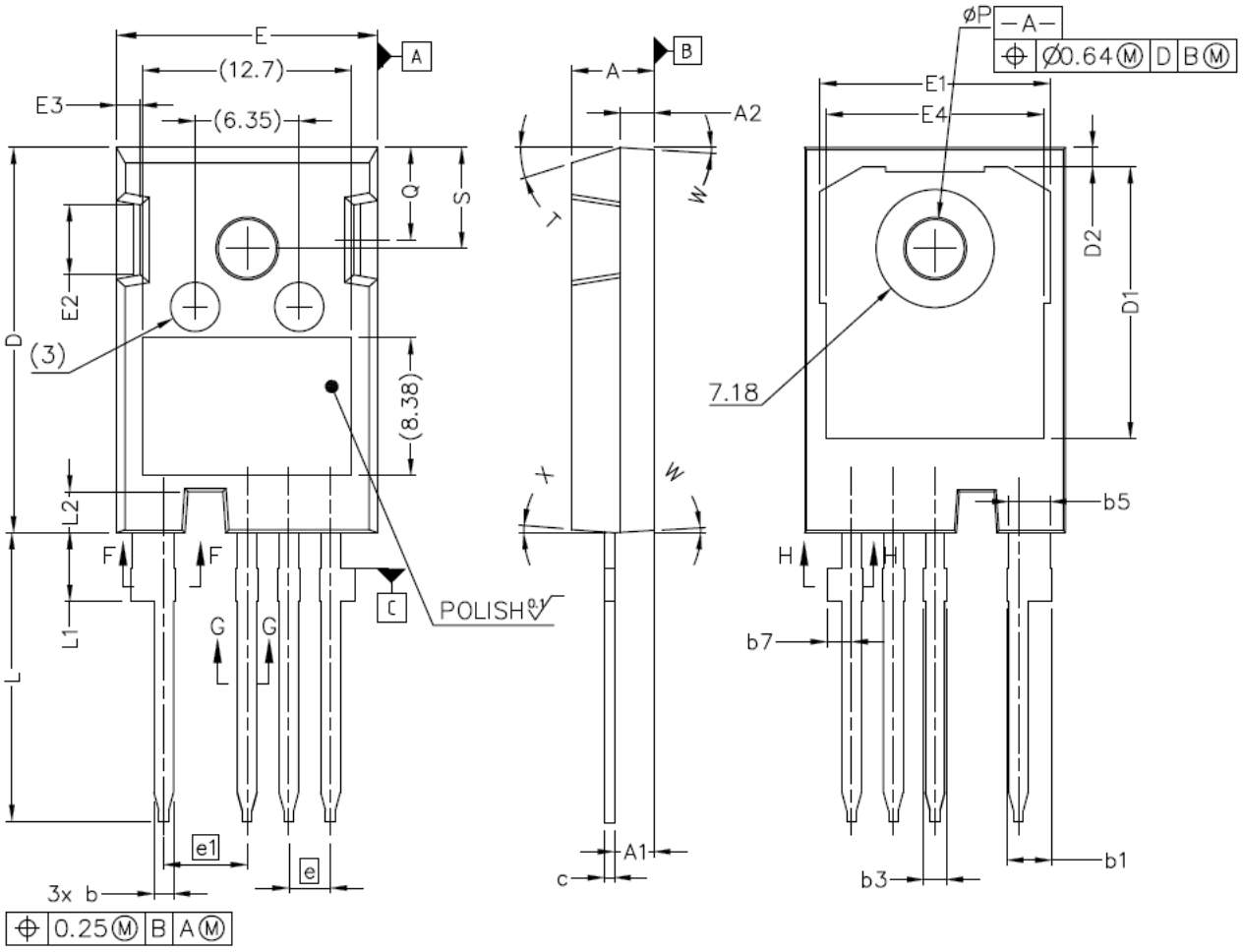
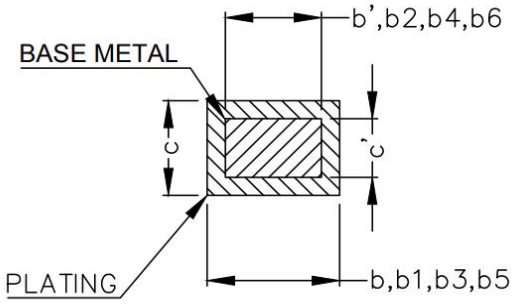


Figure 29. V_{GS} Waveform Example

Package Dimensions

Package TO-247H-4L





SECTION "F-F", "G-G" AND "H-H"
SCALE: NONE

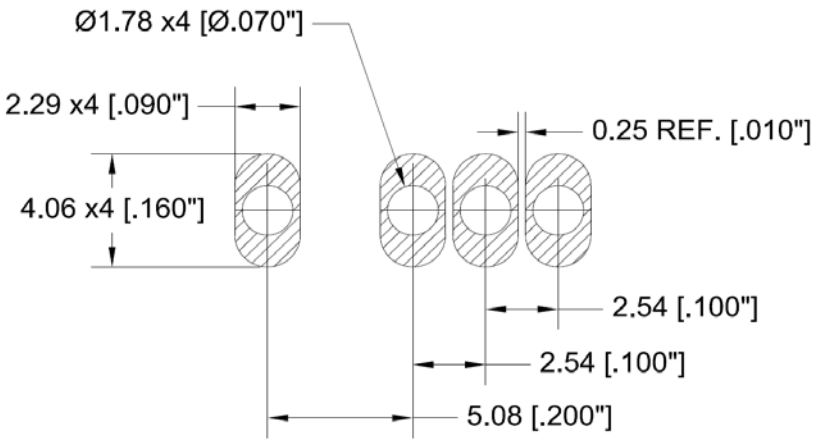
Package Dimensions

Package TO-247H-4L

NOTE ;
1. ALL METAL SURFACES: TIN PLATED, EXCEPT AREA OF CUT
2. DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
3. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
4. 'N' IS THE NUMBER OF TERMINAL POSITIONS

SYM	MILLIMETERS	
	MIN	MAX
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b`	1.07	1.28
b	1.07	1.33
b1	2.39	2.94
b2	2.39	2.84
b3	1.07	1.60
b4	1.07	1.50
b5	2.39	2.69
b6	2.39	2.64
b7	1.30	1.70
c`	0.55	0.65
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.13

SYM	MILLIMETERS	
	MIN	MAX
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	2.54 BSC	
e1	5.08 BSC	
N*	4	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
Ø P	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF.	
W	3.5° REF.	
X	4° REF.	



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■ HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.

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give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

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